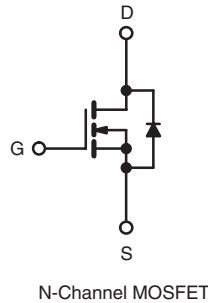


## Power MOSFET

| PRODUCT SUMMARY           |                 |      |
|---------------------------|-----------------|------|
| $V_{DS}$ (V)              | 250             |      |
| $R_{DS(on)}$ ( $\Omega$ ) | $V_{GS} = 10$ V | 0.45 |
| $Q_g$ (Max.) (nC)         | 41              |      |
| $Q_{gs}$ (nC)             | 6.5             |      |
| $Q_{gd}$ (nC)             | 22              |      |
| Configuration             | Single          |      |

**TO-220 FULLPAK**


### FEATURES

- Isolated Package
- High Voltage Isolation = 2.5 kV<sub>RMS</sub> (t = 60 s; f = 60 Hz)
- Sink to Lead Creepage Distance = 4.8 mm
- Dynamic dV/dt Rating
- Low Thermal Resistance
- Lead (Pb)-free Available


**RoHS\***  
COMPLIANT

### DESCRIPTION

Third generation Power MOSFETs from Vishay provide the designer with the best combination of fast switching, ruggedized device design, low on-resistance and cost-effectiveness.

The TO-220 FULLPAK eliminates the need for additional insulating hardware in commercial-industrial applications. The moulding compound used provides a high isolation capability and a low thermal resistance between the tab and external heatsink. This isolation is equivalent to using a 100 micron mica barrier with standard TO-220 product. The FULLPAK is mounted to a heatsink using a single clip or by a single screw fixing.

### ORDERING INFORMATION

|                |                             |
|----------------|-----------------------------|
| Package        | TO-220 FULLPAK              |
| Lead (Pb)-free | IRFI634GPbF<br>SiHFI634G-E3 |
| SnPb           | IRFI634G<br>SiHFI634G       |

### ABSOLUTE MAXIMUM RATINGS $T_C = 25^\circ\text{C}$ , unless otherwise noted

| PARAMETER  | SYMBOL                   | LIMIT                     | UNIT                |                  |
|--|--------------------------|---------------------------|---------------------|------------------|
| Drain-Source Voltage                             | $V_{DS}$                 | 250                       | V                   |                  |
| Gate-Source Voltage                              | $V_{GS}$                 | $\pm 20$                  |                     |                  |
| Continuous Drain Current                         | $V_{GS}$ at 10 V         | $T_C = 25^\circ\text{C}$  | 5.6                 | A                |
|  |                          | $T_C = 100^\circ\text{C}$ | 3.5                 |                  |
| Pulsed Drain Current <sup>a</sup>                |                          | 22                        |                     |                  |
| Linear Derating Factor                           |                          | 0.28                      | W/ $^\circ\text{C}$ |                  |
| Single Pulse Avalanche Energy <sup>b</sup>       | $E_{AS}$                 | 300                       | mJ                  |                  |
| Repetitive Avalanche Current <sup>a</sup>        | $I_{AR}$                 | 5.6                       | A                   |                  |
| Repetitive Avalanche Energy <sup>a</sup>         | $E_{AR}$                 | 3.5                       | mJ                  |                  |
| Maximum Power Dissipation                        | $T_C = 25^\circ\text{C}$ | $P_D$                     | 35                  | W                |
| Peak Diode Recovery dV/dt <sup>c</sup>           |                          | dV/dt                     | 4.8                 | V/ns             |
| Operating Junction and Storage Temperature Range | $T_J, T_{stg}$           |                           | - 55 to + 150       | $^\circ\text{C}$ |
| Soldering Recommendations (Peak Temperature)     | for 10 s                 |                           | 300 <sup>d</sup>    |                  |
| Mounting Torque                                  | 6-32 or M3 screw         |                           | 10                  | lbf · in         |
|  |                          |                           | 1.1                 | N · m            |

#### Notes

- Repetitive rating; pulse width limited by maximum junction temperature (see fig. 11).
- $V_{DD} = 50$  V, starting  $T_J = 25^\circ\text{C}$ , L = 15 mH,  $R_G = 25 \Omega$ ,  $I_{AS} = 5.6$  A (see fig. 12).
- $I_{SD} \leq 5.6$  A,  $dI/dt \leq 120$  A/ $\mu\text{s}$ ,  $V_{DD} \leq V_{DS}$ ,  $T_J \leq 150^\circ\text{C}$ .
- 1.6 mm from case.

\* Pb containing terminations are not RoHS compliant, exemptions may apply

| THERMAL RESISTANCE RATINGS       |            |      |      |      |
|----------------------------------|------------|------|------|------|
| PARAMETER                        | SYMBOL     | TYP. | MAX. | UNIT |
| Maximum Junction-to-Ambient      | $R_{thJA}$ | -    | 65   | °C/W |
| Maximum Junction-to-Case (Drain) | $R_{thJC}$ | -    | 3.6  |      |

| SPECIFICATIONS $T_J = 25\text{ }^\circ\text{C}$ , unless otherwise noted |                     |   |  |      |      |           |               |
|--|---------------------|---|--|------|------|-----------|---------------|
| PARAMETER  | SYMBOL              | TEST CONDITIONS   |  | MIN. | TYP. | MAX.      | UNIT          |
| <b>Static</b>  |                     |   |  |      |      |           |               |
| Drain-Source Breakdown Voltage   | $V_{DS}$            | $V_{GS} = 0\text{ V}, I_D = 250\text{ }\mu\text{A}$   |  | 250  | -    | -         | V             |
| $V_{DS}$ Temperature Coefficient   | $\Delta V_{DS}/T_J$ | Reference to $25\text{ }^\circ\text{C}$ , $I_D = 1\text{ mA}$   |  | -    | 0.30 | -         | V/°C          |
| Gate-Source Threshold Voltage  | $V_{GS(th)}$        | $V_{DS} = V_{GS}, I_D = 250\text{ }\mu\text{A}$   |  | 2.0  | -    | 4.0       | V             |
| Gate-Source Leakage  | $I_{GSS}$           | $V_{GS} = \pm 20\text{ V}$  |  | -    | -    | $\pm 100$ | nA            |
| Zero Gate Voltage Drain Current  | $I_{DSS}$           | $V_{DS} = 250\text{ V}, V_{GS} = 0\text{ V}$  |  | -    | -    | 25        | $\mu\text{A}$ |
|  |                     | $V_{DS} = 200\text{ V}, V_{GS} = 0\text{ V}, T_J = 125\text{ }^\circ\text{C}$   |  | -    | -    | 250       |               |
| Drain-Source On-State Resistance   | $R_{DS(on)}$        | $V_{GS} = 10\text{ V}$  | $I_D = 3.4\text{ A}^b$   | -    | -    | 0.45      | $\Omega$      |
| Forward Transconductance   | $g_{fs}$            | $V_{DS} = 50\text{ V}, I_D = 3.4\text{ A}^b$  |  | 2.5  | -    | -         | S             |
| <b>Dynamic</b>   |                     |   |  |      |      |           |               |
| Input Capacitance  | $C_{iss}$           | $V_{GS} = 0\text{ V},$<br>$V_{DS} = 25\text{ V},$<br>$f = 1.0\text{ MHz}$ , see fig. 5  |  | -    | 770  | -         | pF            |
| Output Capacitance   | $C_{oss}$           |   |  | -    | 190  | -         |               |
| Reverse Transfer Capacitance   | $C_{rss}$           |   |  | -    | 52   | -         |               |
| Drain to Sink Capacitance  | $C$                 | $f = 1.0\text{ MHz}$  |  | -    | 12   | -         |               |
| Total Gate Charge  | $Q_g$               | $V_{GS} = 10\text{ V}$  | $I_D = 5.6\text{ A}, V_{DS} = 200\text{ V},$<br>see fig. 6 and 13 <sup>b</sup> | -    | -    | 41        | nC            |
| Gate-Source Charge   | $Q_{GS}$            |   |  | -    | -    | 6.5       |               |
| Gate-Drain Charge  | $Q_{GD}$            |   |  | -    | -    | 22        |               |
| Turn-On Delay Time   | $t_{d(on)}$         | $V_{DD} = 125\text{ V}, I_D = 5.6\text{ A},$<br>$R_G = 12\text{ }\Omega, R_D = 22\text{ }\Omega,$<br>see fig. 10 <sup>b</sup> |  | -    | 9.6  | -         | ns            |
| Rise Time  | $t_r$               |   |  | -    | 21   | -         |               |
| Turn-Off Delay Time  | $t_{d(off)}$        |   |  | -    | 42   | -         |               |
| Fall Time  | $t_f$               |   |  | -    | 19   | -         |               |
| Internal Drain Inductance  | $L_D$               | Between lead,<br>6 mm (0.25") from<br>package and center of<br>die contact  |  | -    | 4.5  | -         | nH            |
| Internal Source Inductance   | $L_S$               |   |  | -    | 7.5  | -         |               |
| <b>Drain-Source Body Diode Characteristics</b>                           |                     |   |  |      |      |           |               |
| Continuous Source-Drain Diode Current                                    | $I_S$               | MOSFET symbol<br>showing the<br>integral reverse<br>p - n junction diode  |  | -    | -    | 5.6       | A             |
| Pulsed Diode Forward Current <sup>a</sup>                                | $I_{SM}$            |   |  | -    | -    | 22        |               |
| Body Diode Voltage   | $V_{SD}$            | $T_J = 25\text{ }^\circ\text{C}, I_S = 5.6\text{ A}, V_{GS} = 0\text{ V}^b$   |  | -    | -    | 2.0       | V             |
| Body Diode Reverse Recovery Time   | $t_{rr}$            | $T_J = 25\text{ }^\circ\text{C}, I_F = 5.6\text{ A}, dI/dt = 100\text{ A}/\mu\text{s}^b$                                      |  | -    | 220  | 440       | ns            |
| Body Diode Reverse Recovery Charge                                       | $Q_{rr}$            |   |  | -    | 1.2  | 2.4       | $\mu\text{C}$ |
| Forward Turn-On Time   | $t_{on}$            | Intrinsic turn-on time is negligible (turn-on is dominated by $L_S$ and $L_D$ )   |  |      |      |           |               |

**Notes**

- a. Repetitive rating; pulse width limited by maximum junction temperature (see fig. 11).  
b. Pulse width  $\leq 300\text{ }\mu\text{s}$ ; duty cycle  $\leq 2\%$ .

**TYPICAL CHARACTERISTICS** 25 °C, unless otherwise noted

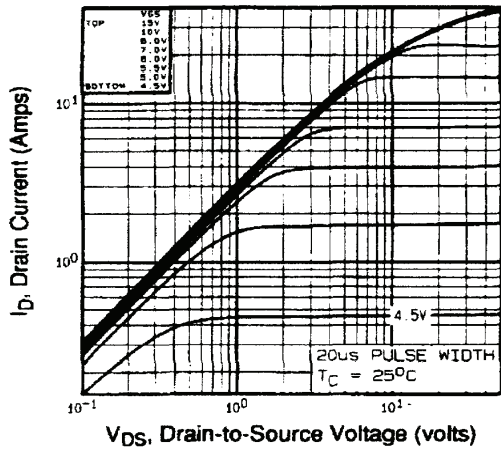


Fig. 1 - Typical Output Characteristics,  $T_C = 25\text{ }^\circ\text{C}$

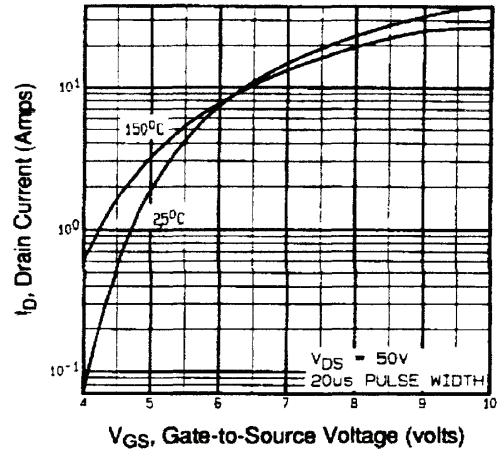


Fig. 3 - Typical Transfer Characteristics

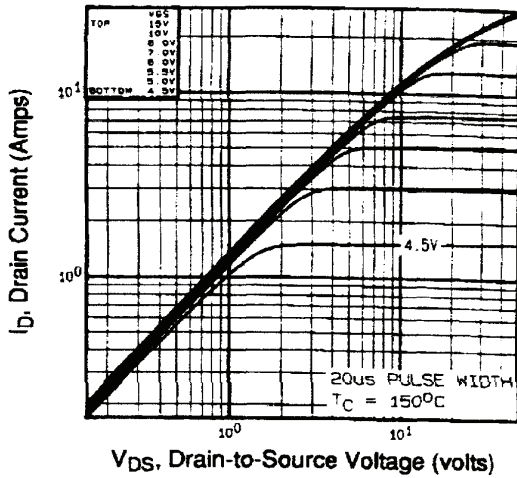


Fig. 2 - Typical Output Characteristics,  $T_C = 150\text{ }^\circ\text{C}$

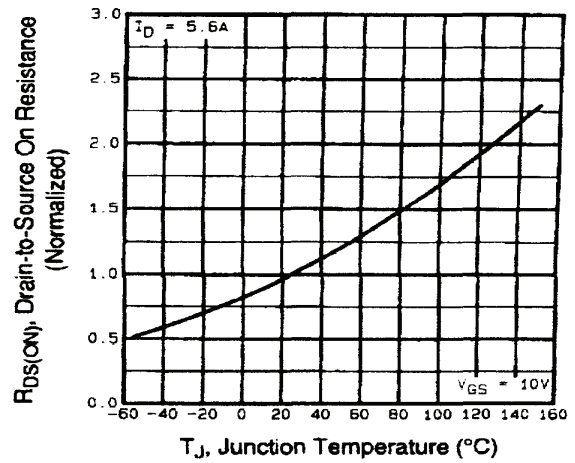


Fig. 4 - Normalized On-Resistance vs. Temperature

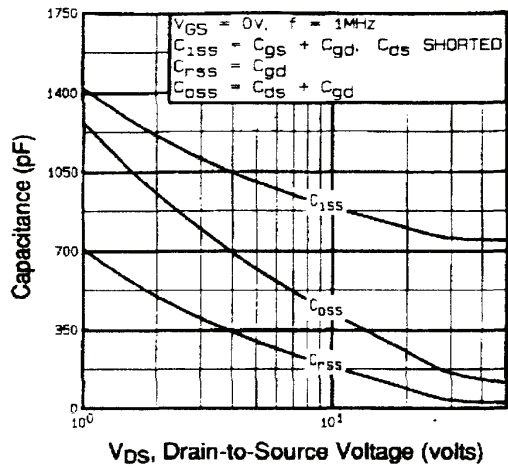


Fig. 5 - Typical Capacitance vs. Drain-to-Source Voltage

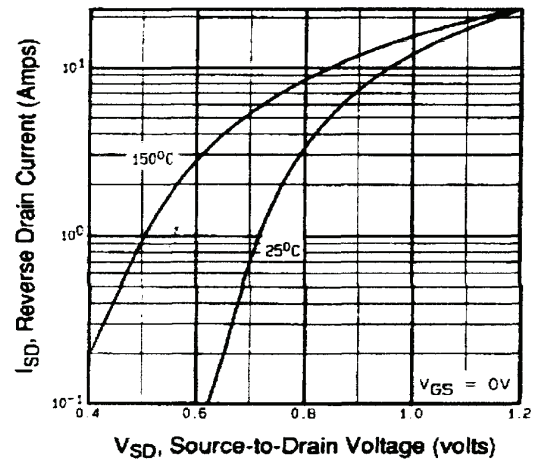


Fig. 7 - Typical Source-Drain Diode Forward Voltage

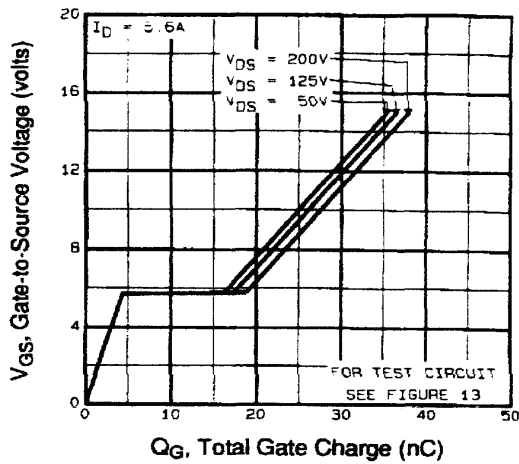


Fig. 6 - Typical Gate Charge vs. Gate-to-Source Voltage

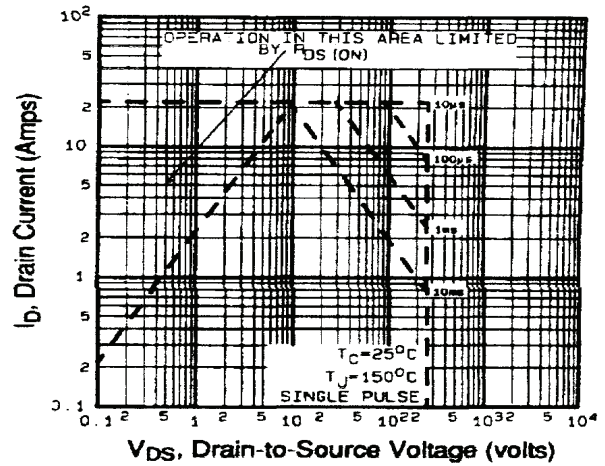


Fig. 8 - Maximum Safe Operating Area

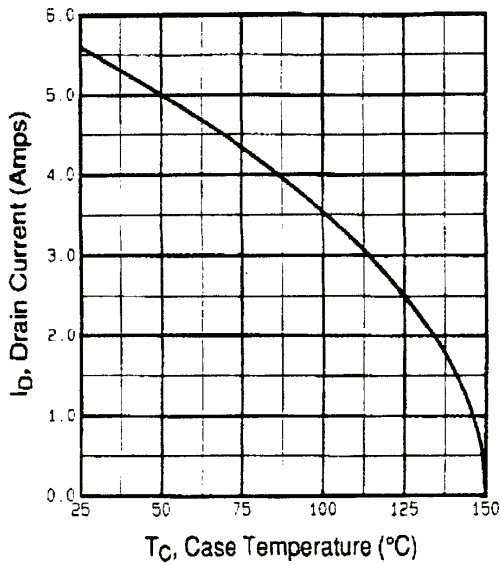


Fig. 9 - Maximum Drain Current vs. Case Temperature

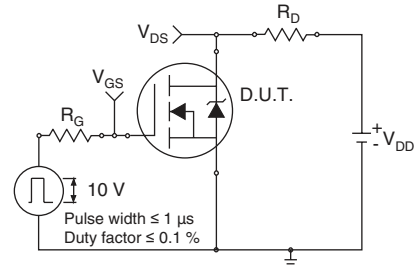


Fig. 10a - Switching Time Test Circuit



Fig. 10b - Switching Time Waveforms

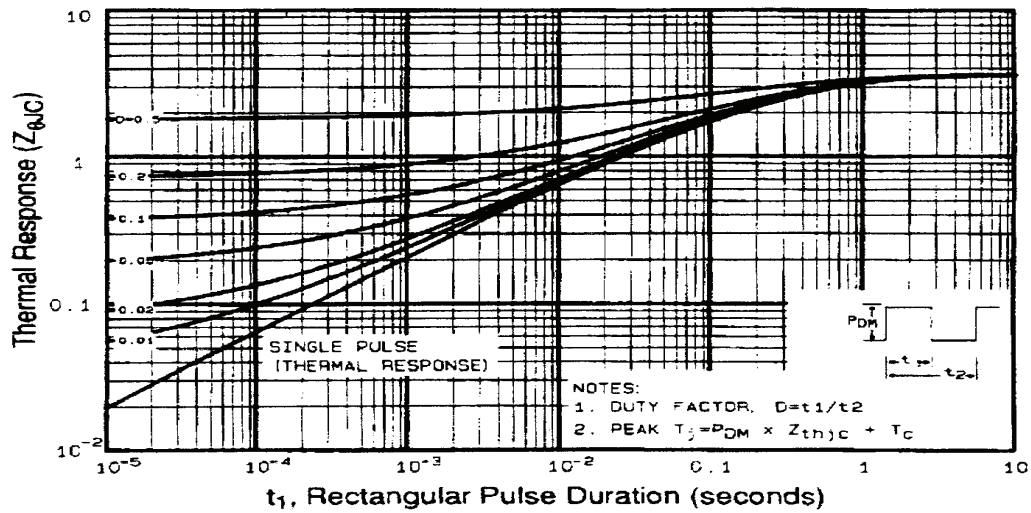


Fig. 11 - Maximum Effective Transient Thermal Impedance, Junction-to-Case

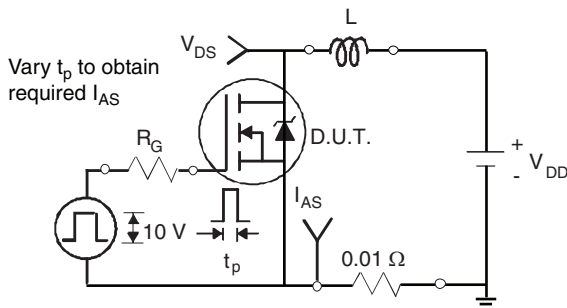


Fig. 12a - Unclamped Inductive Test Circuit

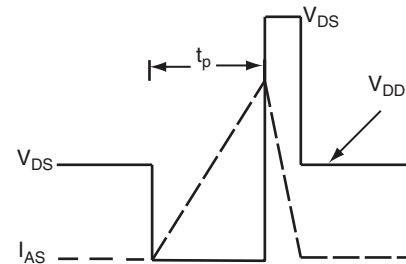


Fig. 12b - Unclamped Inductive Waveforms

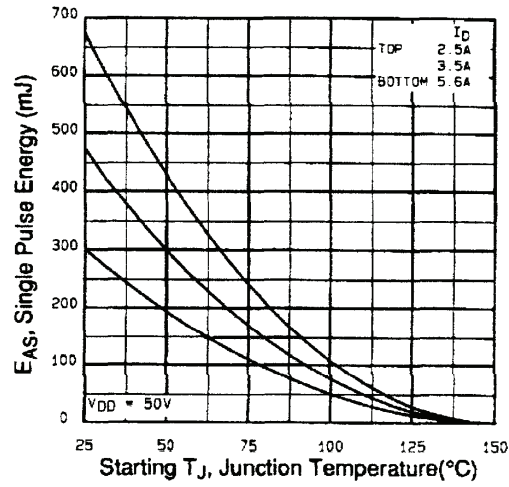


Fig. 12c - Maximum Avalanche Energy vs. Drain Current

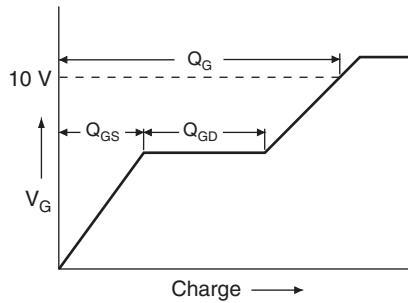


Fig. 13a - Basic Gate Charge Waveform

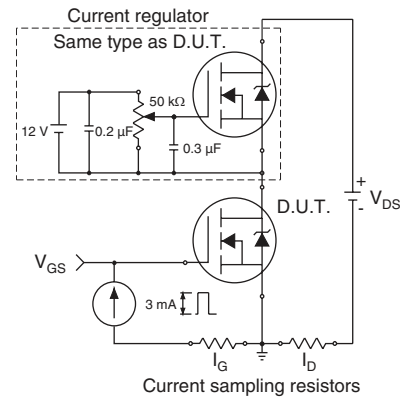
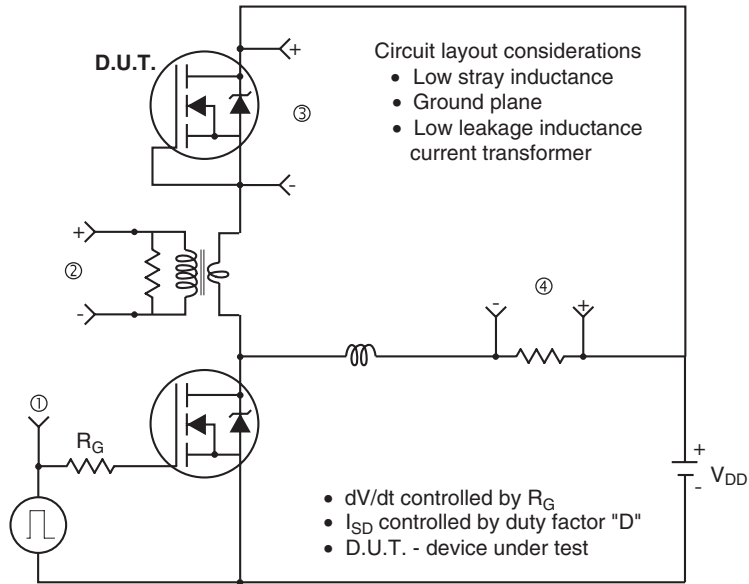


Fig. 13b - Gate Charge Test Circuit

## Peak Diode Recovery dV/dt Test Circuit



\*  $V_{GS} = 5\text{ V}$  for logic level devices and  $3\text{ V}$  drive devices

**Fig. 14 - For N-Channel**

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